

Amendments to the Specification:

IN THE SPECIFICATION:

Please replace the paragraph at page 1, lines 2-5 with the following rewritten paragraph:

This is a Division of Application No. 10/102,878 filed March 22, 2002 issued as U.S. Patent 6,642,651 B2 on November 4, 2003, which in turn is a Division of Application No. 09/284,802 filed April 21, 1999 issued as U.S. Patent 6,380,672 B1 on April 30, 2002, which in turn is a U.S. National Stage of PCT/JP98/03699, filed August 20, 1998. The entire disclosure of the prior applications is hereby incorporated by reference herein in its entirety.

Please replace paragraphs [0017] and [0039] as follow:

[0017] It is preferable in the present invention that the upper insulating layer be deposited in an inner region of the lower insulating layer so as to have a width narrower than that of the ~~upper~~ lower insulating layer. Such a two-step configuration prevents contact of the upper insulating layer formed of an organic material with the organic semiconductive film; hence deterioration of the organic semiconductive film can be more securely prevented. In such a two-step configuration, both the lower insulating layer and the upper insulating layer may be formed of inorganic materials.

[0039] Each pixel 7 is provided with a conduction control circuit 50 that supplies scanning signals through a scanning line *gate*, and a thin film luminescent device 40 emitting light on the basis of image signals supplied from a data line *sig* through the conduction control circuit 50. In this embodiment, the conduction control circuit 50 includes a first TFT 20 that supplies a scanning signal to a gate electrode through a scanning line *gate*, ~~s~~ a holding capacitor *cap* for holding an image signal supplied from a data line *sig* through the first TFT 20, and a second TFT 30 that supplies the image signal held in the holding capacitor *cap* to the gate electrode. The second TFT 30 and the thin film luminescent device 40 are connected in series between an opposite electrode *op* and a common feed line *com*. The holding capacitor *cap* may be formed between the opposite electrode *op* and the scanning line *gate*, in addition to between the opposite electrode *op* and the common feed line *com*.